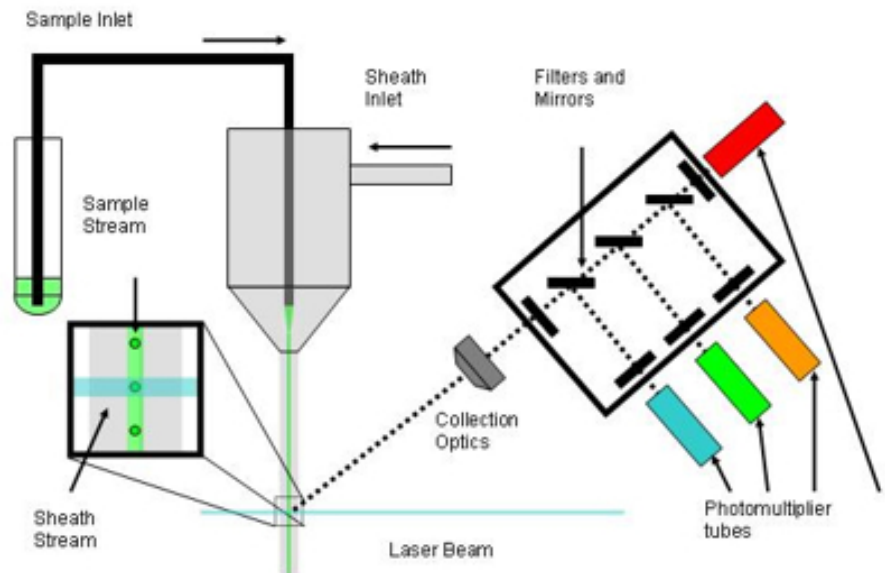


Lecture 3

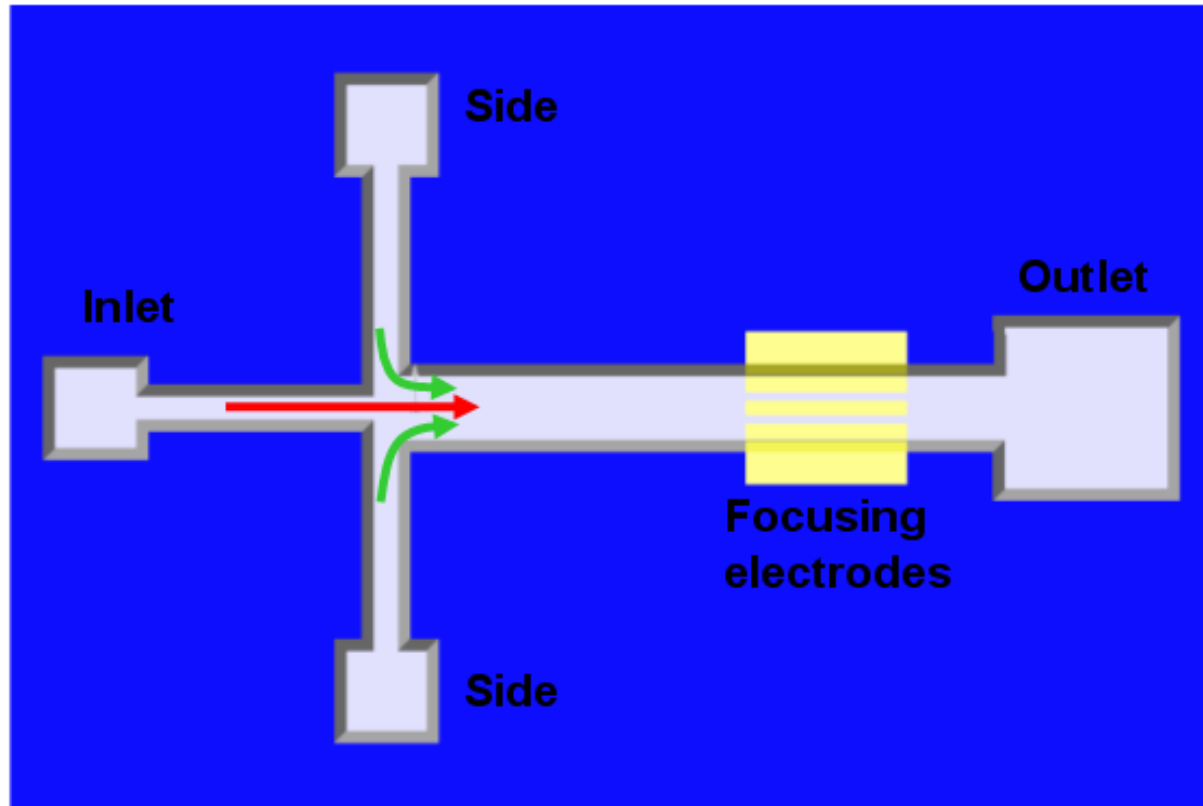
Project Description & Process Flow

Flow Cytometry

Flow cytometry is an important bioanalytical technique that is used for sorting and counting of cells, measurements of physical and chemical characteristics of cells etc.

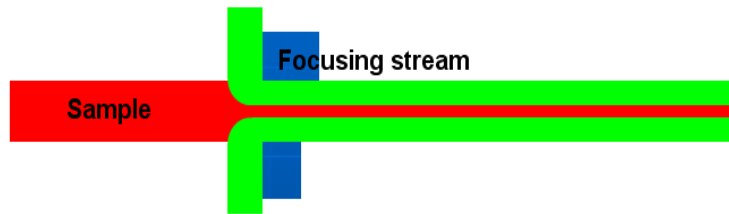


Flow Cytometer /Molecular Focusing on a Chip

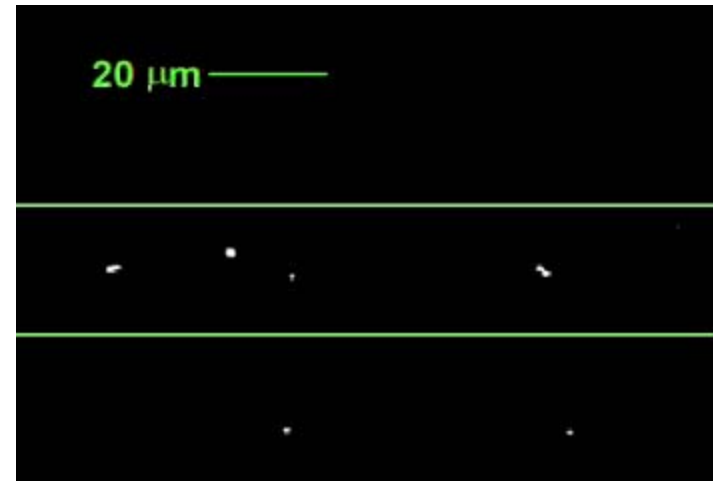
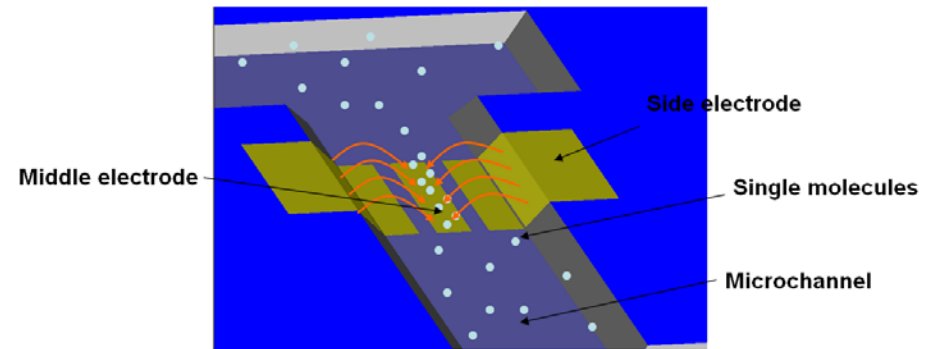


Hydrodynamic Focusing and Electrokinetic Focusing

Hydrodynamic Focusing:

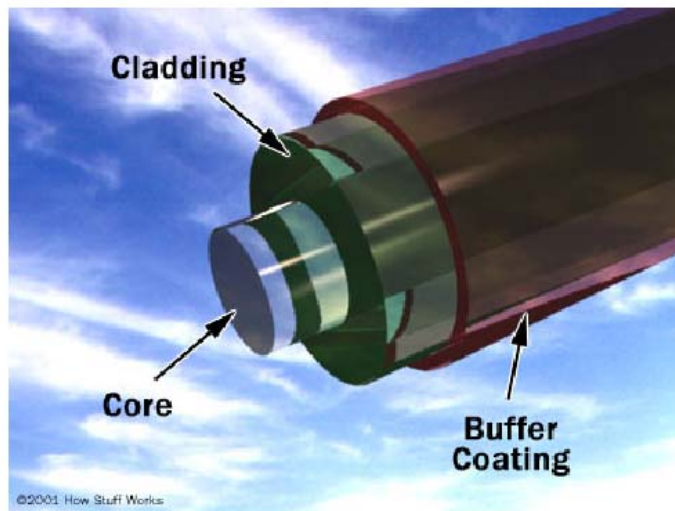


Electrokinetic focusing:

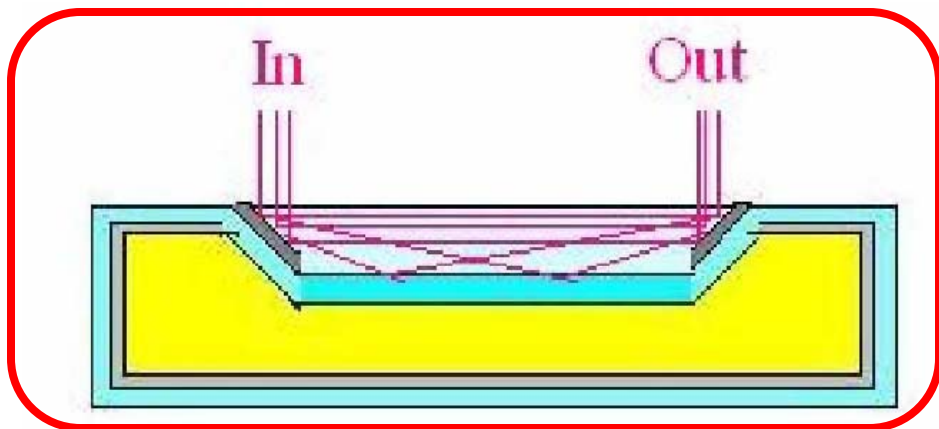
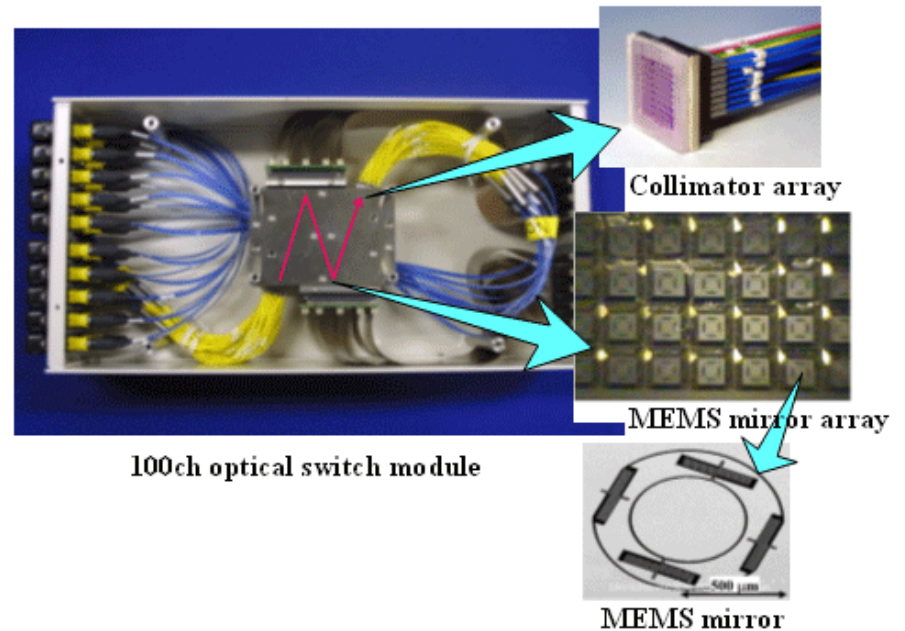
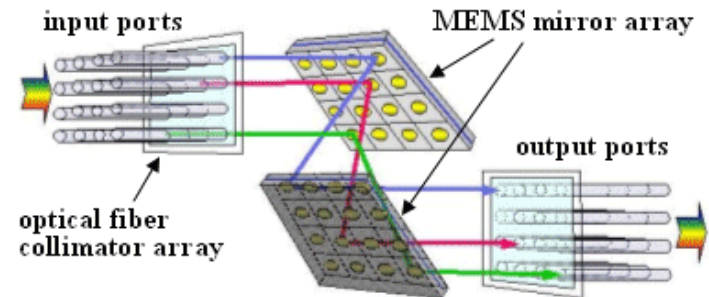
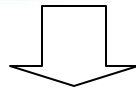


Optical Waveguide on a Chip

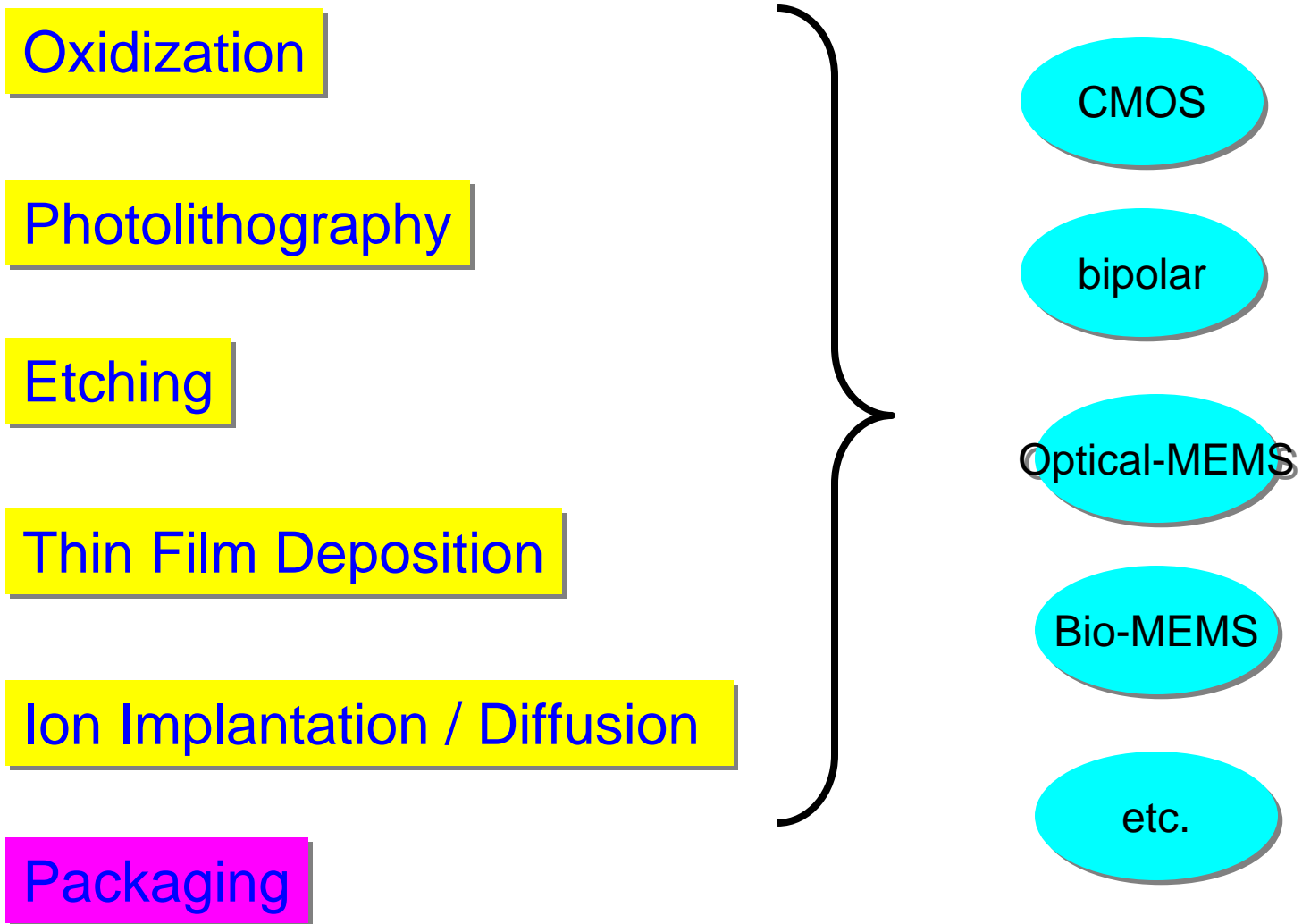
Optical waveguides are widely used, especially in the form of optical fibers, for long distance, high data rate telecommunications.



©2001 How Stuff Works

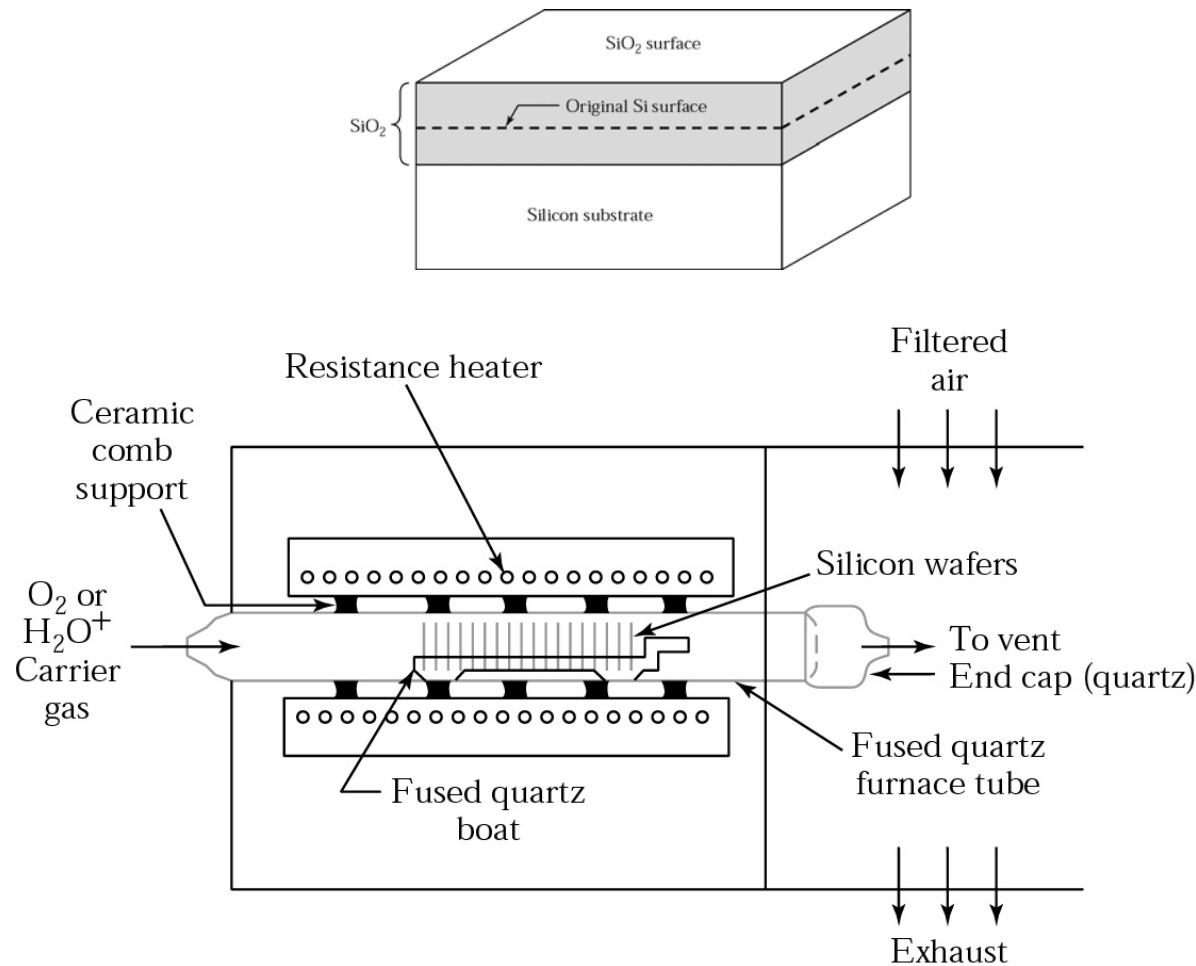


Basic Microfabrication Steps

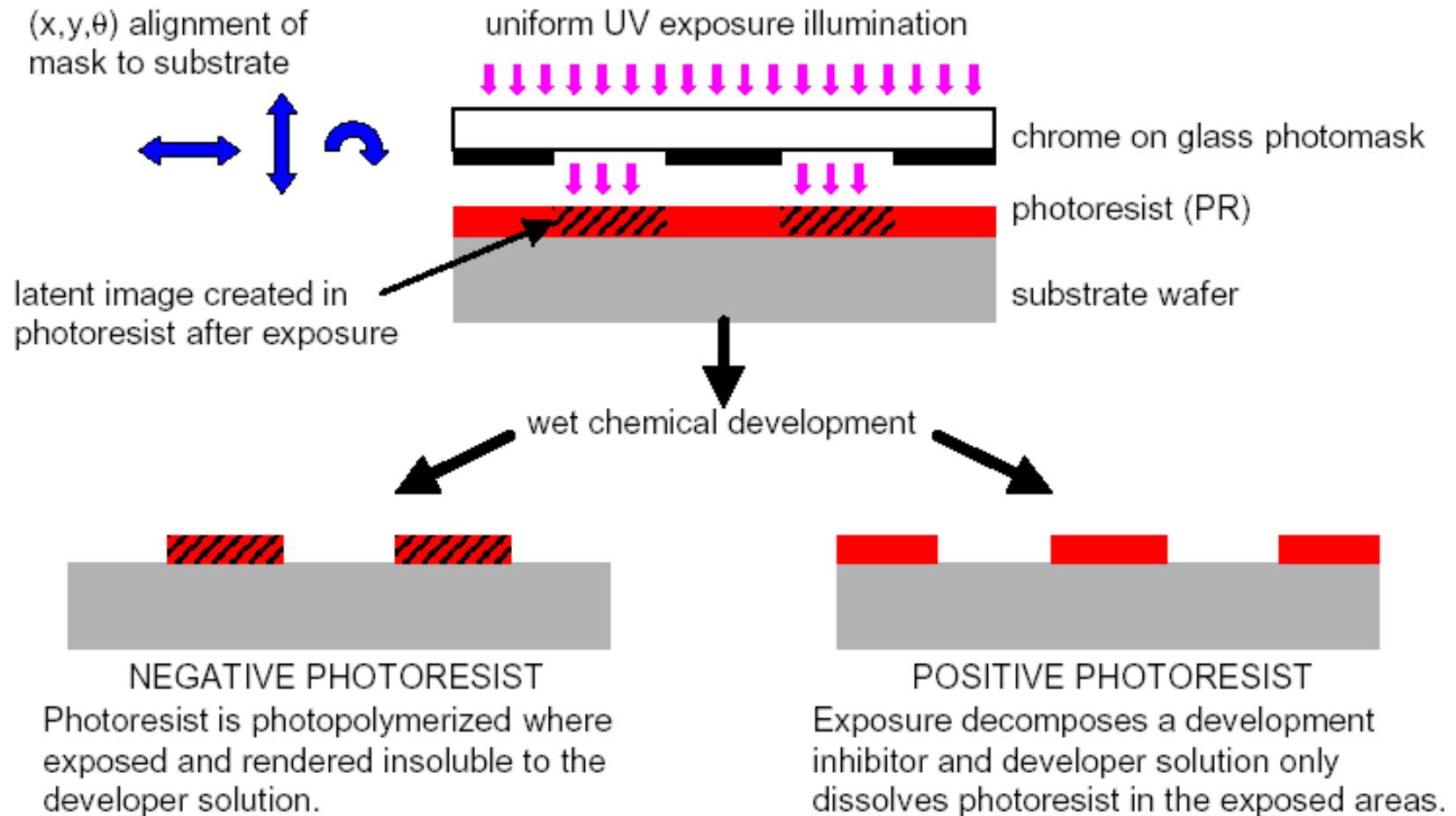


Thermal Oxidization

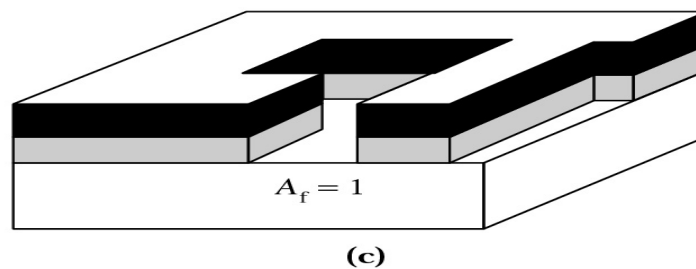
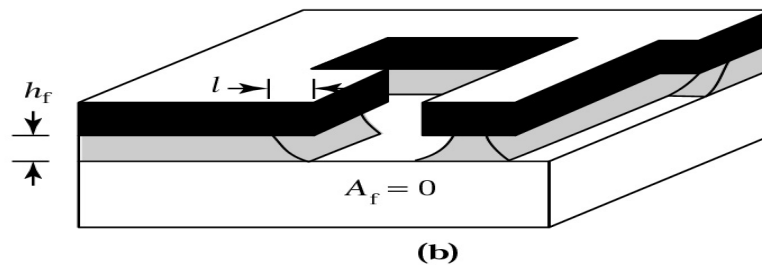
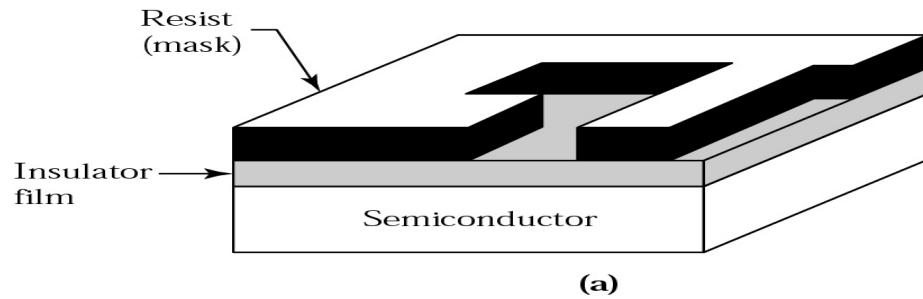
- Dry Oxidization : $\text{Si (solid)} + \text{O}_2 \text{ (gas)} \rightarrow \text{SiO}_2 \text{ (solid)}$
- Wet Oxidization: $\text{Si (solid)} + 2\text{H}_2\text{O (gas)} \rightarrow \text{SiO}_2 \text{ (solid)} + 2\text{H}_2 \text{ (gas)}$



Photolithography

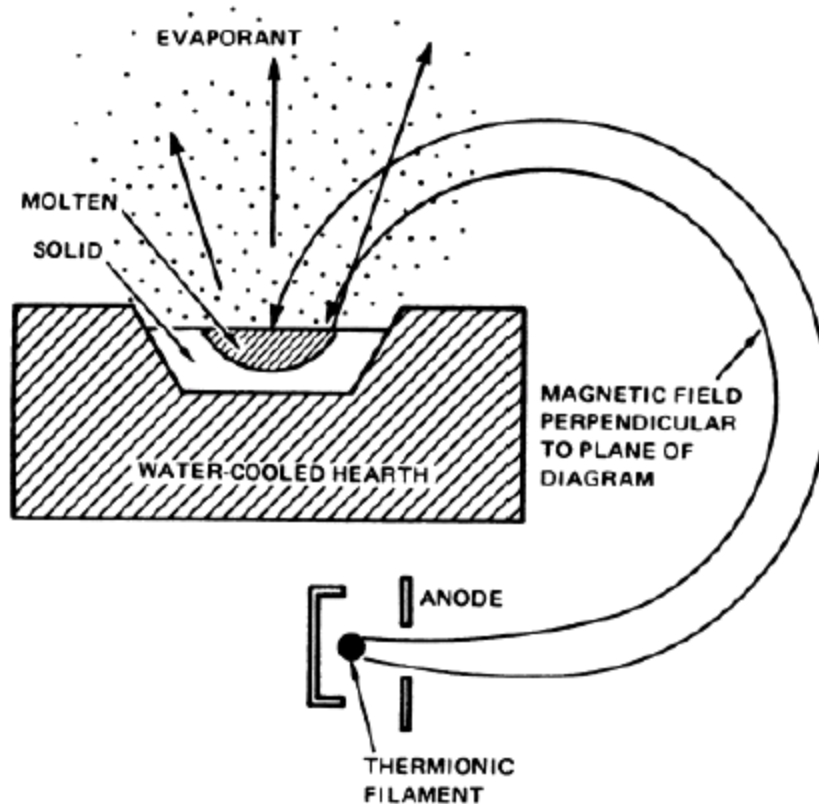


Etching



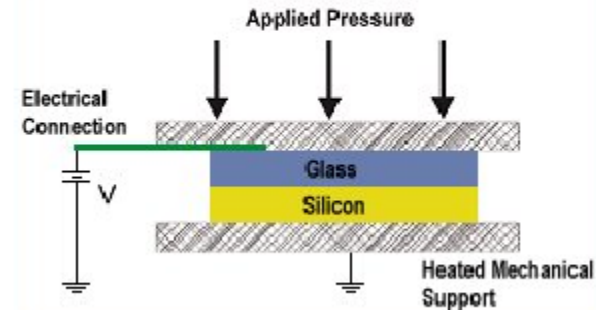
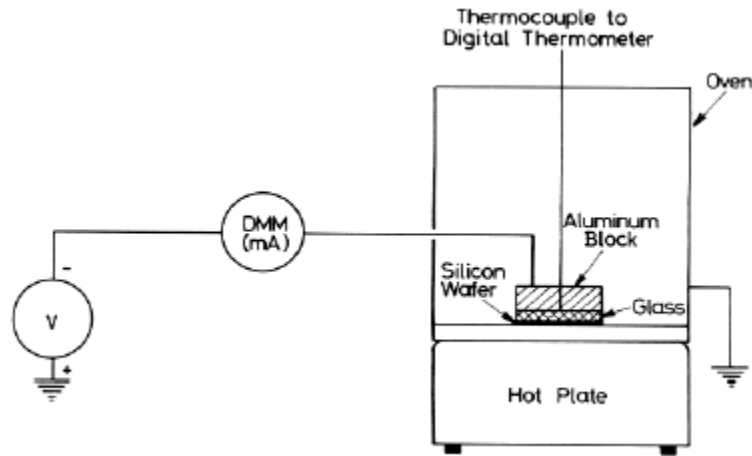
- Wet etch vs Dry Etch
- Etch Selectivity
- Etch Rate
- Degree of Anisotropy

Thin Film Deposition : Evaporation



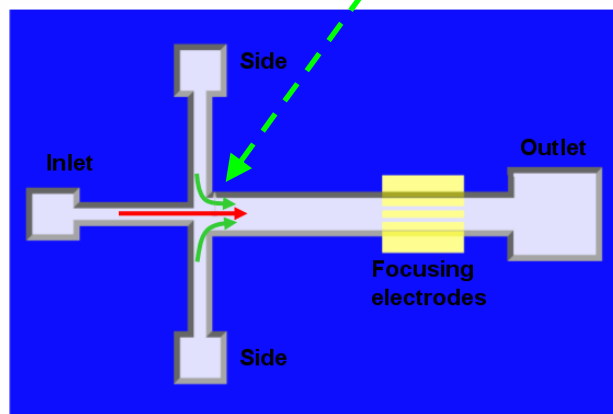
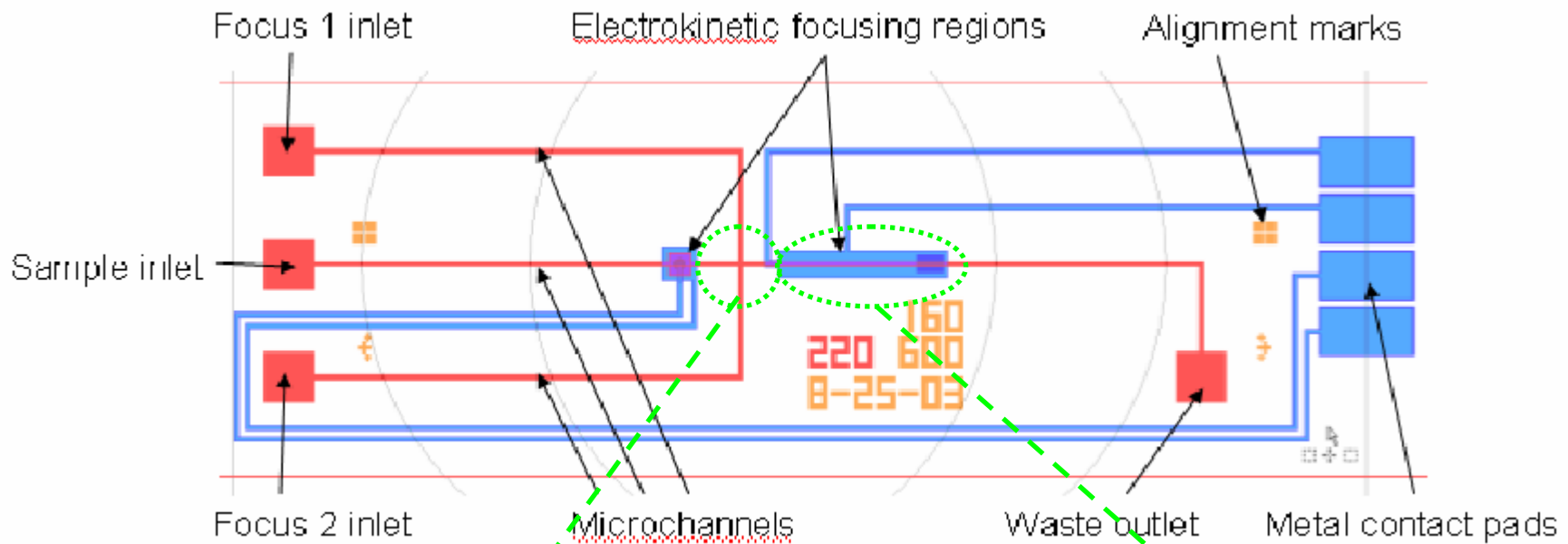
- Focused beam of electrons are used to locally heat the source
- Can be used to heat/evaporate even high melting point materials

Packaging: Anodic Bonding

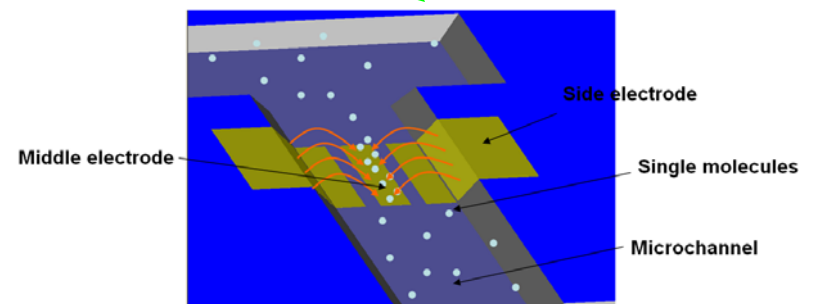


- High voltage (300 -1000 V) generates large electrostatic forces
- High temperature (300-600 C) facilitates bonding
- Bonds SiO_2 to Si or metal
 - Use Pyrex 7740 or Borofloat glass to match thermal expansion coefficient

Layout of Flow Cytometer (FC)



Electrokinetic focusing:



Process Flow for Flow Cytometer (FC)

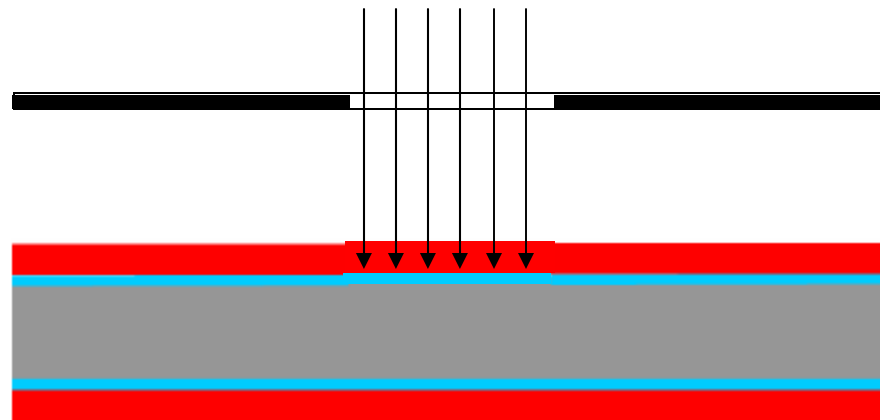
1. Oxidation of silicon substrate (Lab done by staff)

- Grow 0.5~1 μ m oxide on silicon surface



2. Patterning the oxide with mask #1 (Lab #2_FC)

- 2 μ m PR 1813 used as mask
- Buffered HF (BOE) used for wet etching
- Wafer backside also protected by PR 1813 (manually applied)



(positive PR)

3. Substrate bulk etching (Lab #3_FC)

- Concentrated KOH used for wet etching
- Temperature control required
- Channel width: 120 ~ 150 μm , depth: ~ 20 μm



4. Second oxidation (Lab #4_FC)

- Grow 0.5 μm oxide for electrode isolation purpose



5. Metallization by thermal evaporation (Lab #5_FC)

- 2500 \AA aluminum film deposited as electrodes
- 10 ~ 20 μm PR SJR5740 photoresist deposition on fresh aluminum



6. Patterning metal by aluminum etchant (Lab #6_FC)

- Photolithography using electrodes mask
- PAN etchant used to remove unwanted aluminum
- Electrodes spacing: $50\mu\text{m}$



7. Removal of oxide on after patterning with mask #3 (Lab #7_FC)

- $10\mu\text{m}$ PR SJR5740 used as mask (Al attacked by BOE)
- Buffered HF used as etchant



8. Anodic bonding with pre-drilled glass plate (Lab #8_FC)
- Pyrex 7740 glass used to seal the microchannels



Process Flow for Flow Cytometer (FC)

Silicon oxidation
Lab # 2_WG



Photoresist
deposition (back
and front)
Lab # 3_WG



Front side
lithography
Lab # 3_WG



Buffered Oxide etch
Lab # 3_WG



Anisotropic silicon
KOH etch
Lab # 4_WG



Cladding Layer
grown
(Thick SiO₂ - wet
oxide)

Lab # 5_WG

Shadow Mask

Aluminum

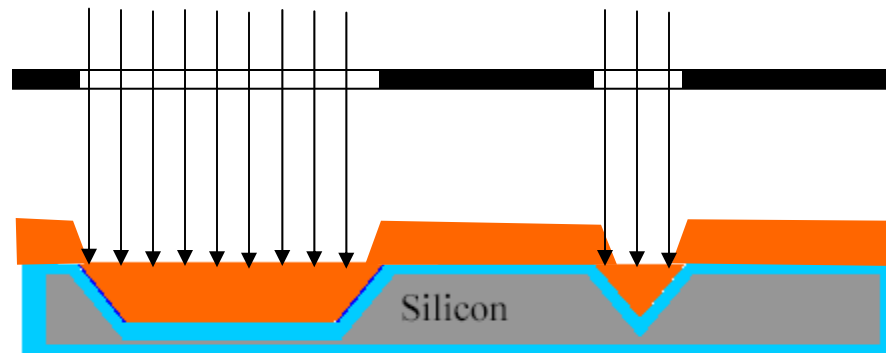
Patterning

Lab # 6_WG



SU-8 Fill
Waveguide
Complete

Lab # 7_WG



SU-8 is negative PR